STEAM "Spline-based Tables for Efficient and Accurate Device-Modelling"

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RRAM Crossbar





High Frequency NPN



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High Frequency NPN



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Image Source: Wikipedia

High Frequency NPN





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32nm planar FET 22nm tri-gate FET





Image Source: Wikipedia

RRAM Crossbar **High Frequency NPN** Metallic Top Electrode Switching Medium **Bottom Electrode** 1 function MOD = BSIM3v3_2_4_ModSpec(uniqID) ... 1348 32nm planar FET 22nm tri-gate FET 1349 1350 E function vecLim = initGuess(u, MOD) ... % initGuess 1793 1794 1795 function vecLim = limiting... 1796 ÷ (vecX, vecY, vecXold, vecYold, u, MOD) ... % limiting 2300 2301 ⊞ function [fe, qe, fi, qi] = fqei_all(vecX, vecY, vecLim, u, flag, MOD)... 2302 5088 1 function MOD = BSIM3v3 2 4d ModSpec(uniqID) ... 458 459 If function [fgei out, J out] = fgeiJ(vecX, vecY, vecLim, vecU, flag, MOD) 489

 490
 function [fe_, qe_, fi_, qi_,...

 491
 d_fe_d_X_, d_qe_d_X_, d_fi_d_X_, d_qi_d_X_,...

 492
 d_fe_d_Y_, d_qe_d_Y_, d_fi_d_Y_, d_qi_d_Y_] = ...

 493
 ⊞
 fqei_dfqeidXYU(vecX_, vecY_, MOD)....

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Image Source: Wikipedia





Simulator (equation engine...) gives v_{pn}, v_{in}



i_{pn}: "explicit output"



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i_{pn}: "explicit output" v_{pn}: "other IO"









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Simulator (equation engine...) gives v_{pn}, v_{in} It wants i_{pn} to solve a system of equations! Usually, it also wants some derivatives We want some sort of Look-Up table to give us i_{pn} and derivatives





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32 nm Planar Transistors



22 nm Tri-Gate Transistors



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Model parameters,

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Model parameters, Internal unknown(s),

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Model parameters, Internal unknown(s), Other IO(s), ...

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Machine Translation is openly available – VAPP

tion is VAPP Qi Qi Qe fi MODSPEC











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Linear extrapolation is an option











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Speedup Accuracy Memory

Simulation Results

Test Circuits and Waveforms











Speedup Evaluation

Speedup Evaluation

Core device evaluation BSIM 100-150X, MVS 20-40X
Speedup Evaluation



Speedup Evaluation



AC 7-10X, TRANSIENT 6-8X

Speedup Evaluation



Core device evaluation BSIM < 0.00001% MVS < 0.001%







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Spline evaluation Table sizes and computation times

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- Exploiting structure in the polynomial coefficients obtained from tablebased modelling
- Simulating circuits with measurement data!

QUESTIONS